SQJ160EP

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COMPLIANT

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Automotive N-Channel 60 V (D-S) 175 °C MOSFET

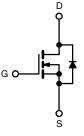


Top View

PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0020
I _D (A)	362
Configuration	Single

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested • Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ160EP (for detailed order number please see <u>www.vishay.com/doc?79776</u>)

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise notec	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	v	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	T _C = 25 °C	la la	362		
Continuous drain current	T _C = 125 °C	I _D	209		
Continuous source current (diode conduction)		I _S	400	А	
Pulsed drain current ^a		I _{DM}	426		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	50		
Single pulse avalanche energy	L = 0.1 IIIH	E _{AS}	125	mJ	
Max for the second distribution	T _C = 25 °C	р	500	W	
Maximum power dissipation	T _C = 125 °C	P _D	166	vv	
Operating junction and storage temperature ra	ange	T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^c			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	42	°C/W
Junction-to-case (drain)		R _{thJC}	0.3	0/10

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT				
Static											
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v				
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.2	2.8	3.5	v				
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA				
		$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 60 V -		-	1					
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA				
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250					
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α				
		$V_{GS} = 10 V$	I _D = 15 A	-	0.0014	0.0020					
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 15 A, T _J = 125 °C	-	-	0.0032	Ω				
		$V_{GS} = 10 \text{ V}$	I _D = 15 A, T _J = 175 °C	-	-	0.0040					
Forward transconductance ^b	g _{fs}	V _{DS}	-	150	-	S					
Dynamic ^b	<u>.</u>	<u>.</u>			-						
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	4873	6697	pF				
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	1955	2727					
Reverse transfer capacitance	C _{rss}			-	140	196					
Total gate charge ^c	Qg		V _{DS} = 30 V, I _D = 10 A	-	79	119	nC				
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$		-	24	-					
Gate-drain charge ^c	Q _{gd}			-	18	-					
Gate resistance	Rg	f = 1 MHz		0.4	0.9	1.4	Ω				
Turn-on delay time ^c	t _{d(on)}			-	19	29	- ns				
Rise time ^c	t _r		$V_{DD} = 30 \text{ V}, \text{ R}_{\text{I}} = 3.0 \Omega$		12	18					
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10$ Å, $V_{GEN} = 10$ V, $R_g = 1$ Ω		-	33	50					
Fall time ^c	t _f				10	15					
Source-Drain Diode Ratings and Chara	acteristics ^b	<u>.</u>			-						
Pulsed current ^a	I _{SM}			-	-	426	А				
Forward voltage	V _{SD}	I _F = 10 A, V _{GS} = 0 V		-	-	1.1	V				
Body diode reverse recovery time	t _{rr}	- I _F = 10 A, dl/dt = 100 A/μs		-	56	112	ns				
Body diode reverse recovery charge	Q _{rr}			-	56	112	nC				
Reverse recovery fall time	t _a			-	25	-					
Reverse recovery rise time	t _b		-	33	-	ns					
Body diode peak reverse recovery current	I _{RM(REC)}			-	1.7	-	А				

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

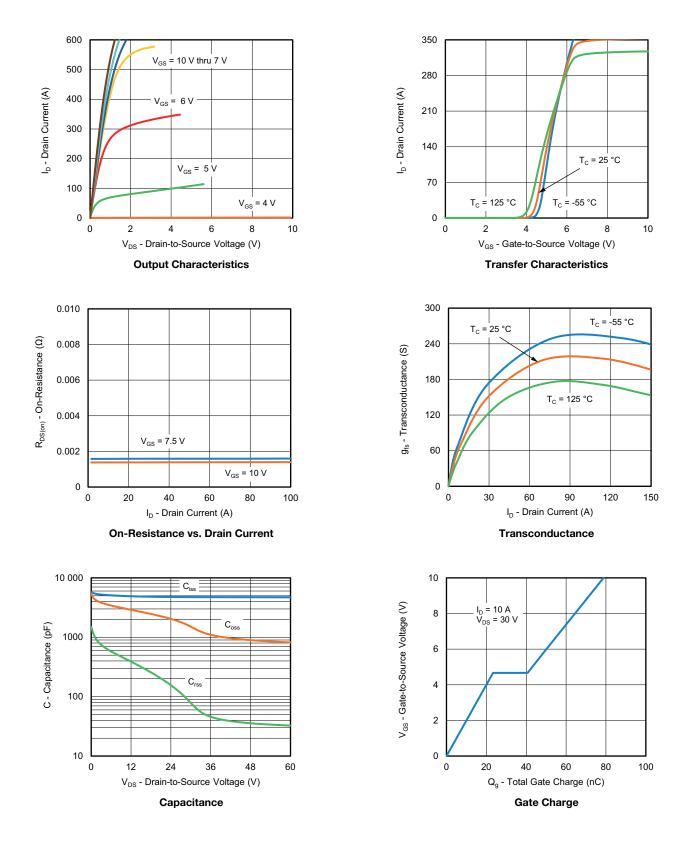
b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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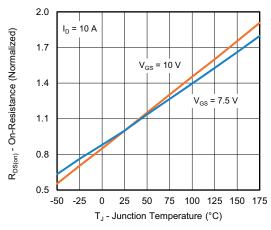
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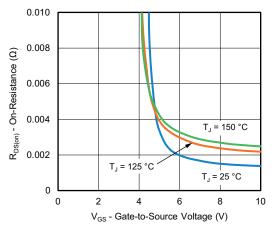
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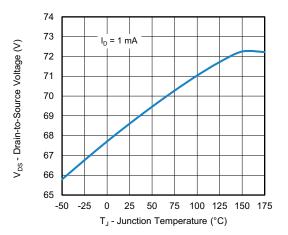
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



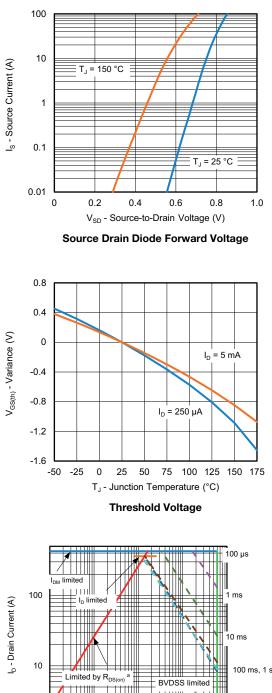
On-Resistance vs. Junction Temperature

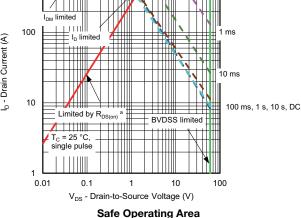


On-Resistance vs. Gate-to Source Voltage



Drain Source Breakdown vs. Junction Temperature





a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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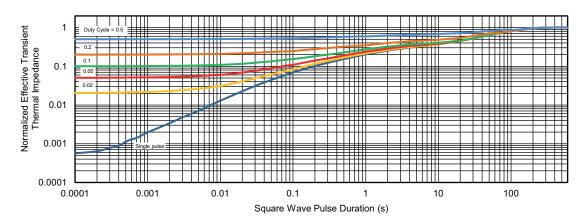
Note

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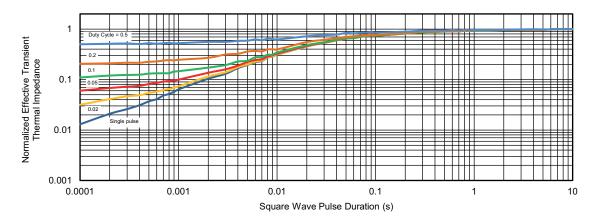
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

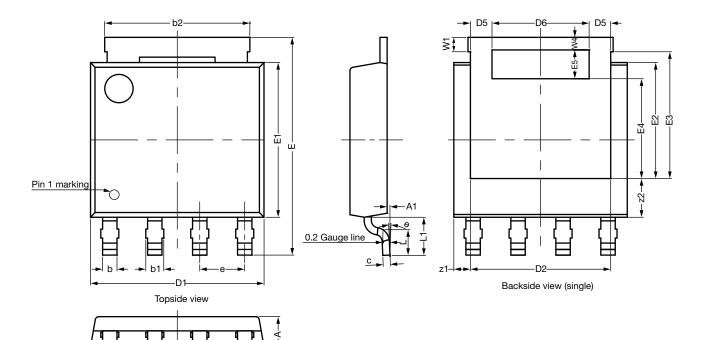
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63107.

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PowerPAK[®] SO-8L (PPKSO8LWLA) Case Outline 3



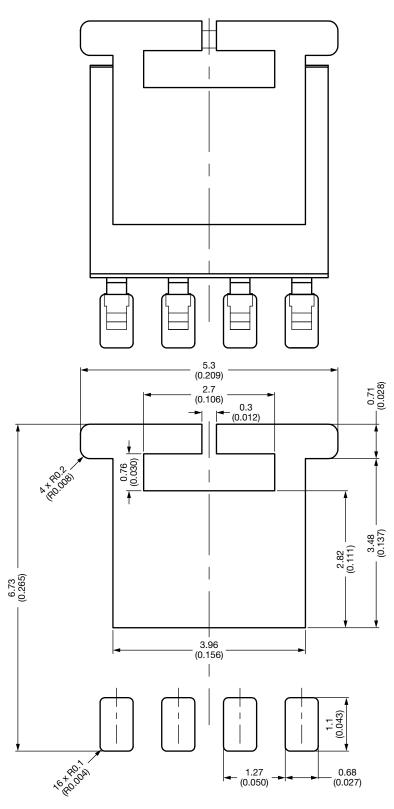
DIM.		MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
А	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

Note

• Millimeter will govern



Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)

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Document Number: 78020



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